

The Effect of Annealing on the Structural and Optical Properties of Mn₂O₃ Thin Film Prepared by Chemical Spray Pyrolysis

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Abstract: Thin films of Mn₂O₃ are synthesized using a simple chemical spray pyrolysis method on substrate from glass and then annealed in 400°C for one hour in air. By using the X-ray diffraction we characterize the structure properties of the deposited films. The results indicate that the films are polycrystalline with cubic structure with a strong (222) preferred orientation. Atomic force microscope (AFM) was used to study morphological properties of the samples. By using UV-VIS spectrometer the energy band gap and optical constants were calculated.

Keywords: chemical spray pyrolysis, Mn₂O₃, Structural and Optical Properties

1. Introduction

Manganese Oxide was a transition metal oxide. Cubic (Mn₂O₃), tetragonal Mn₃O₄ and cubic MnO structures. Among these oxide, Dimanganese trioxide Mn₂O₃ is most stable. Manganese oxide thin films can be applied as rechargeable batteries, catalysts, electrochemical capacitors, sensors and magneto electronic devices.[1] Different structural, electronic, and magnetic properties of manganese oxides are fundamentally influenced by several oxidation conditions and locations of the manganese ions in the unit cell of these oxides. Various process employed to produce manganese oxide films, such as sputtering, electron beam evaporation, pulse laser deposition molecular beam epitaxy, electrochemical, spray pyrolysis, and sol-gel[2,3]. The spray pyrolysis technology has the merit of low cost, easy to use, safe and appropriate for scientific studies. Some papers notify on the output of manganese oxide thin films by spray pyrolysis and their optical and electrical properties. The optical properties of Mn₂O₃, Mn₃O₄ and MnO were calculated and it was established that the not filled orbits of the transition oxides thin films have optical energy band gaps in the visible region. Mn₂O₃ has comparatively high conductivity, p-type semiconductor, thermodynamic stability[4,5].

2. Experimental

Mn₂O₃ thin films were prepared by chemical spray pyrolysis technique. We use the aqueous solution consist of 0.1M of manganese acetate tetra hydrate (Mn(C₂H₃O₂)₂·4H₂O) as a precursor salt, and 50mL from deionized water as a solvent, homogeneous mixture was accomplished by employing magnetic stirrer. Ultrasonically (Model SB-200 DTDN) glass slides were cleaned then put on a solid uniform thermal conductor surface to supply convenient heating with consistency to films. A heater was applied as heat source to supply temperature of around 250°C. The typical conditions were the following parameters, spray time (15 sec), average deposition (10 cm³/min), distance between nozzle and substrate (30 ± 1cm). Thicknesses of the patterns were evaluated using the weighing technique and the thicknesses

of the prepared films were (600±20)nm. The prepared films were then annealed at 400°C for 1 h and allowed to cool for room temperature. To study the structural properties of the prepared samples we use x-ray diffraction type Philips with the following specifications: target CU, wavelength: 1.5406 Å. The optical measurements comprise measuring the absorbance and transmittance with range from (300-900) by using UV-VIS spectrophotometer type Jenway 6800.

Sample	hkl	2θ(deg)	d(Å)	FWHM(deg)	G(nm)
Mn ₂ O ₃ before annealing	222	33.0565	2.7076	0.3425	24.2
	321	36.0245	2.4911	0.3250	
Mn ₂ O ₃ after annealing	222	33.0580	2.7075	0.3031	27.4
	321	35.4753	2.5284	0.1356	

3. Results and Discussion

3.1. Structural and morphological properties

Fig. 1 showed the X-ray diffraction of Mn₂O₃ films before and after annealing, all the peaks are sharp it is evident that the films deposited are polycrystalline in nature and the positions of X-ray diffraction peaks fit well with the cubic structure with preferred orientation (222) corresponding to ASTM cards no: 41-1442. The peaks exhibit small increasing in the intensity with increasing temperature. The average grain size of Mn₂O₃ thin film samples were calculated by employing the Scherrer's equation,[6].

$$D = 0.94\lambda / \beta \cos\theta \dots\dots\dots(1)$$

The crystallite size of the films prepared was shown in Table 1.

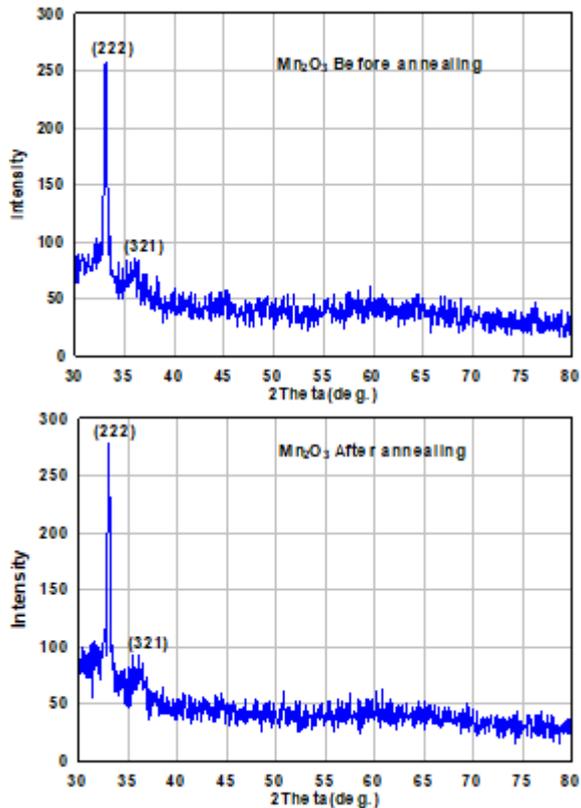


Figure 1: XRD patterns of thin films

Fig.2 display 3-D images AFM of Mn₂O₃ thin films before and after annealing. The growth in average diameter grain due to increase in annealing temperature is clearly seen from the AFM image. The average diameter of grain of the composed films was found to be in the range of (204-219)nm

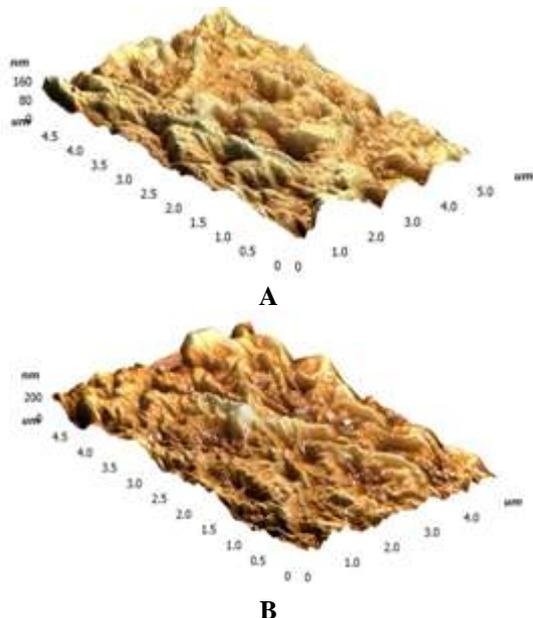


Figure 2: 3D AFM images of deposited thin film, A before annealing, B after annealing

3.2 Optical properties

We study The optical absorption spectrum of the prepared films in the range of (300- 900 nm) before and after annealing shown in Fig.(3).It is obvious that Both the films

have a high optical absorbance in the visible region, which decreases gradually as the wavelength increases, we can notice the Absorbance increases for annealed film and shifted to longer wavelengths. This may be attributed to the creation of levels at the energy band by increasing temperature and this leads to the shift of peak to smaller energies.

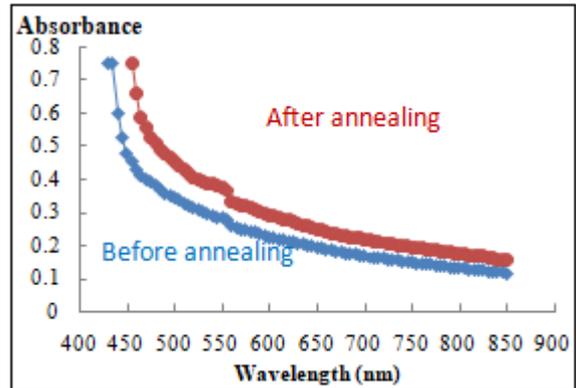


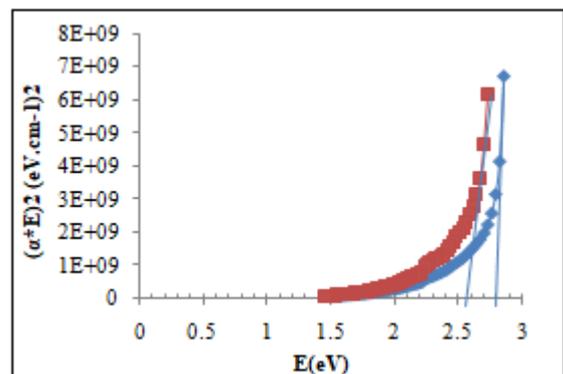
Figure 3: Absorption spectrum for Mn₂O₃ thin films

The optical energy band gap E_g of the assembled thin films was calculated, by using the following equation [7].

$$\alpha h\nu = A(h\nu - E_g)^n \text{-----(2)}$$

Where A is constant, $h\nu$ is the incident photon energy, and (n) is a factor whose value dependent on the nature of band transition, $n = 1/2$ or $3/2$ for direct allowed and direct forbidden transition. The values of direct optical band gap was found to be 2.8 eV for Mn₂O₃ before annealing and 2.4 eV after annealing, and the indirect optical band gap was found to be 2.4 eV for Mn₂O₃ film before annealing and 2.2 eV for annealed Mn₂O₃ film which is in agreement with the report[8], which is shown in Fig.(4).the annealing procedure enhance crystallinity and increases average grain size that result is decreasing defects, therefore band gap energy decreased. The extinction coefficient (k) has been premeditated using the following relation[9]and showed in Fig.(5).

$$k = \frac{\alpha\lambda}{4\pi} \text{-----(3)}$$



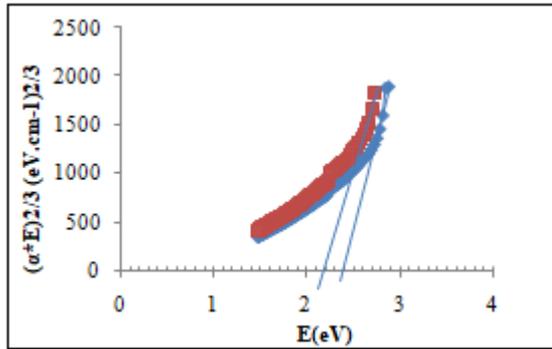


Figure 4: The direct and indirect optical energy band gap for Mn₂O₃ films

We can perceive from Fig.(5) that the extinction coefficient, generally, decreases with the increase of wavelength for all films. Also its value increases by annealing operation. This is ascribing to the same reason introduced earlier in the absorption spectrum. Also we studied the spectrum of the refractive index as be seen in Fig.(6). It can be perceive that the refractive index increases with annealing this is impute to to the increase in the absorbance and decreases in the transmittance. The difference of the real (ϵ_r) and imaginary (ϵ_i) parts of the dielectric constant values facing wavelength before and after annealing are be in view in Fig.(7). The grand ϵ_i values were computed using the formulas[10]

$$\epsilon_r = n^2 - k^2 \quad \dots\dots\dots (4)$$

$$\epsilon_i = 2nk \quad \dots\dots\dots (5)$$

The ϵ_r values are higher than that of ϵ_i values. It is seen that the ϵ_r and ϵ_i values decrease with annealing

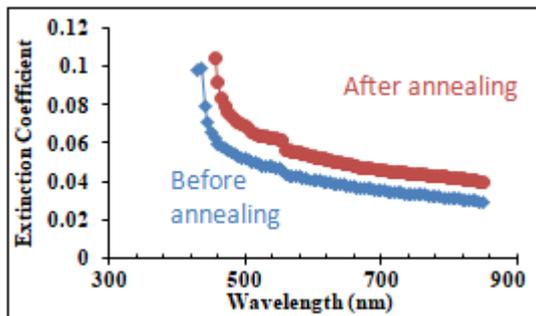


Figure 5: Extinction coefficient spectrum for Mn₂O₃ thin films

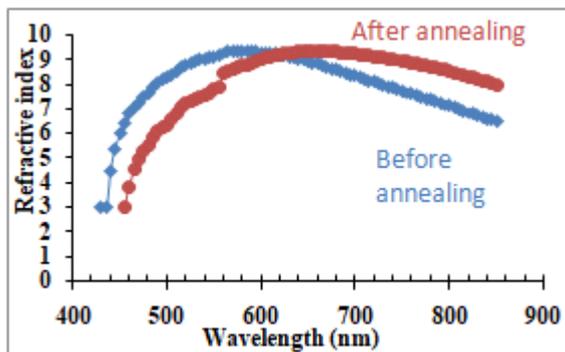


Figure 6: Refractive index as spectrum for Mn₂O₃ films

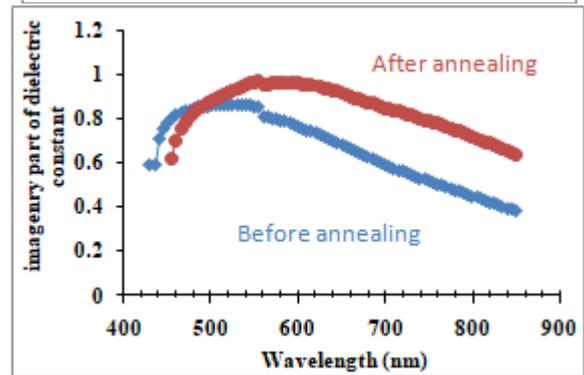
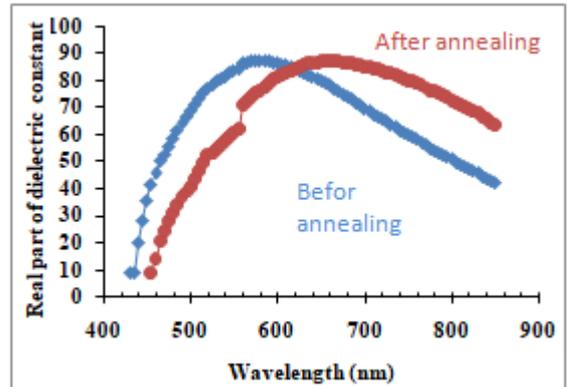


Figure 7: difference of real and imagenary part of dielectric constants a function of wavelength for Mn₂O₃ films

4. Conclusion

Thin films of Dimanganese trioxide Mn₂O₃ with thicknesses of (600±20)nm were arranged by chemical spray pyrolysis method and annealed for one hours with 400°C. The XRD results showed that all films are polycrystalline in nature with a cubic structure and the preferred orientation was along the (222) plane for all films. The absorbance for all prepared films increases as the wavelength increases and The band gap decreases with increasing temperature

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